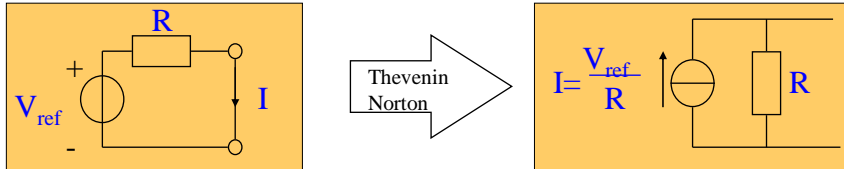


The current source



- Minimum noise equals: $\frac{4kT}{R}$

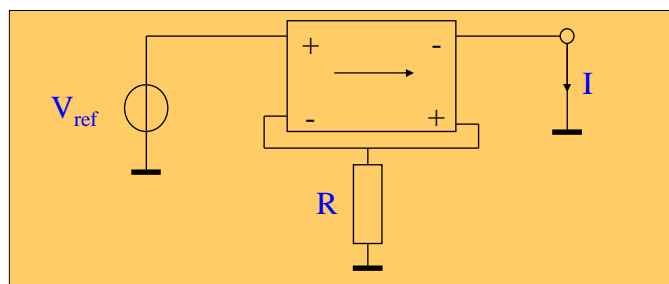
DC current through resistor gives an increase of $1/f$ noise (granular structure)

- Accuracy of source also determined by the accuracy of R
- Output impedance mostly too low



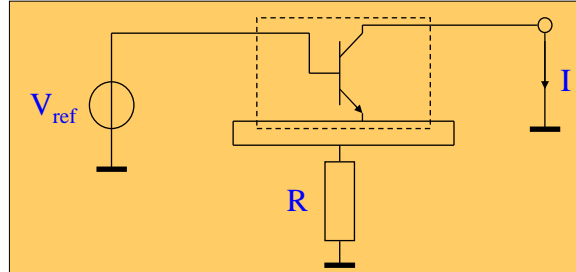
Use active $V \rightarrow I$ converter

The Active Current Source



- Output impedance is
- What about the noise?

Nullor implemented by one CE stage

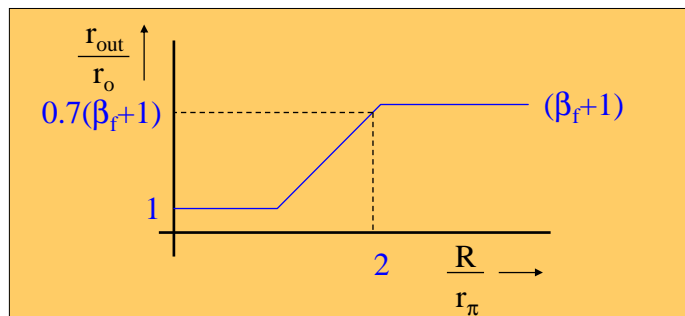


- $I = -(V_{\text{ref}} - V_{\text{BE}})/R$
- Temperature behavior V_{BE} found in I (how to solve?)
- Output impedance:

$$r_{\text{out}} = r_o + R + R \cdot \frac{\beta_f r_o - R}{r_b + r_\pi + R}$$

- If $R \gg r_\pi$ and $R \gg r_b \Rightarrow r_{\text{out}} = (\beta_f + 1)r_o$

Plot of the output impedance vs R



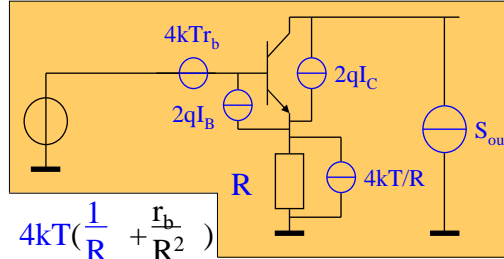
$$V_R = I \cdot R = I \cdot 2r_\pi = 2\beta \frac{kT}{q}$$

$$\beta_f = 100, \quad \frac{kT}{q} = 25 \text{ mV}$$

$$\Rightarrow V_R = 5\text{V}$$

- Lower β_f reduces V_R but also r_{out}
- Better nullor approximation helps (r_o must be increased)

Noise behavior of active current source



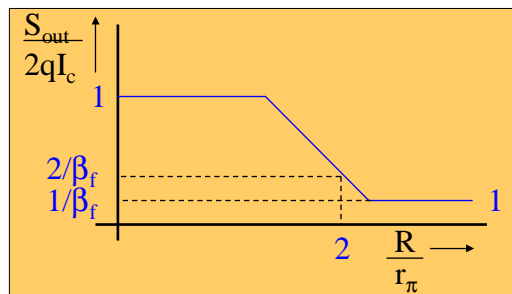
$$S_{out} = \underbrace{\frac{2qI_C}{(1 + \frac{r_\pi}{\beta_f R})^2}}_I + \underbrace{\frac{2qI_B}{(1 + \frac{r_\pi}{\beta_f R})^2}}_II + \underbrace{\frac{4kT(\frac{1}{R} + \frac{r_b}{R^2})}{(1 + \frac{r_\pi}{\beta_f R})^2}}_III$$

$R \rightarrow \text{infinite}$

I \rightarrow 0
 II \rightarrow $2qI_B$
 III \rightarrow 0 ($4kT/R$)

Only base
shot noise
remains

Plot of noise vs R



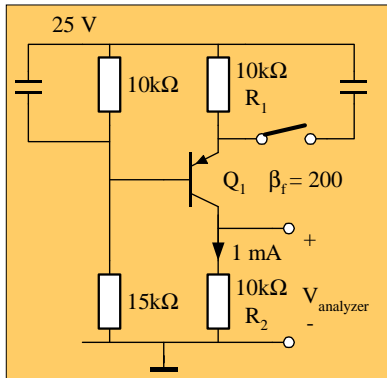
If contribution of $2qI_C$ plus $4kT/R$ equals $2qI_B$, then

$$R = \frac{2\beta_f}{g_m} \Rightarrow V_R = 5 \text{ V} \quad \text{and} \quad S_{out} = 4qI_B = 2 \cdot 2qI_B$$

Lowering β_f for reducing V_R does not help also, as:

$S_{out} = 8kT I/V_R \Rightarrow$ The lower V_R the higher the noise

Current source demo



Switch open:

$$S_{out} \approx 4kT \frac{R_2^2}{R_1} + 4kTR_2 + 2qI_B R_2^2$$

$$\rightarrow v_{n,out} \approx 22 \text{ nV} / \sqrt{\text{Hz}} = -33 \text{ dB}\mu\text{V}$$

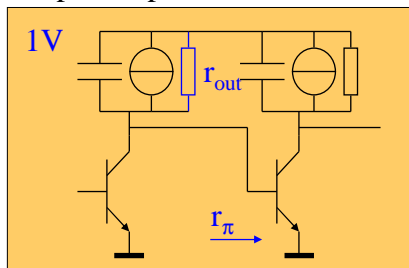
Switch closed:

$$S_{out} \approx 0 + 4kTR_2 + 2qI_C R_2^2$$

$$\rightarrow v_{n,out} \approx \text{ nV} / \sqrt{\text{Hz}} = \text{ dB}\mu\text{V}$$

Current sources in IV circuits

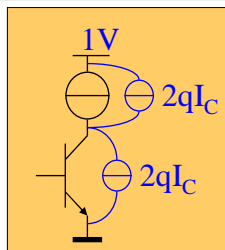
Output impedance:



$$V_R \text{ relatively small} \Rightarrow r_{out} = \frac{V_{AF}}{I_C}$$

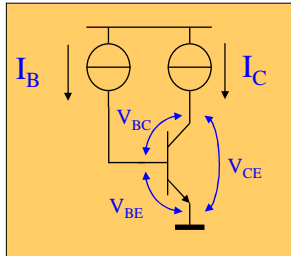
- Reduction of the DC loop gain \Rightarrow accuracy
- Does not need to cost bandwidth as pole also shifts

Noise:



- Noise of the active part approximately doubles

Saturating transistors



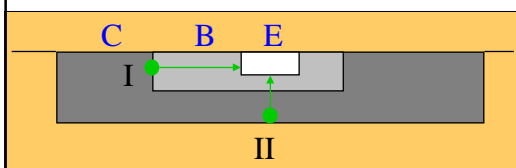
- Transistor saturates if $I_C/I_B < \beta_F$
- Collector-emitter voltage is the difference of V_{BE} and V_{BC}

$$V_{CE} = \frac{kT}{q} \ln \left[\frac{1 + \frac{1}{\beta_r} (1 + I_C / I_B)}{1 - \frac{I_C}{I_B \beta_f}} \right]$$

PTAT

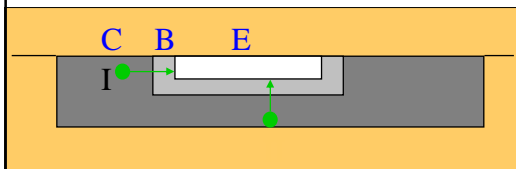
- For $I_C/I_B = \beta_f$ denominator equals zero $\Rightarrow V_{CE}$ not determined
- V_{CE} reduces for larger β_r (saturation voltage reduces)
- V_{CE} reduces for larger I_C/I_B (deeper saturation)

Influence of layout on $V_{saturation}$ (I)



- electron at I has a larger chance on recombination than electron at II
- \Rightarrow Bad for β_r

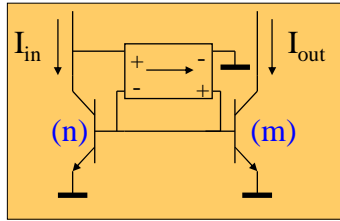
Take care of a large β_r



- Most of the electrons have a short way to go
- \Rightarrow Less recombination
- $\Rightarrow \beta_r$ increases

General: Collector and emitter overlap should be as large as possible

The current mirror



Mirror used for:

- biasing purposes
- current-gain stages
- buffering (cascode)

$$\text{Transfer : } \frac{I_{\text{in}}}{I_{\text{out}}} = \frac{m}{n}$$

Again nullor can be implemented by wire \Rightarrow standard current mirror

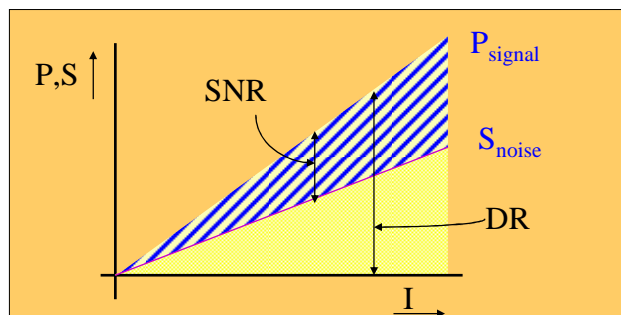
Signal-to-noise ratio and dynamic range of a current mirror

- SNR is the ratio of smallest and largest signal that can be processed at the **same** time
- DR is ratio of smallest and largest signal that can be processed, not necessarily at the **same** time
- Noise power proportional to collector current ($2qI_C$)
- Signal power proportional to the square of IC (I_C^2)

For $I_C=1$ nA
and $B=10$ kHz



SNR = 52dB
DR $\rightarrow \infty$

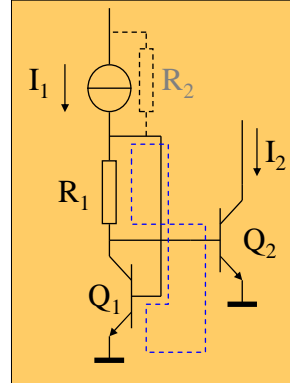


Peaking current source

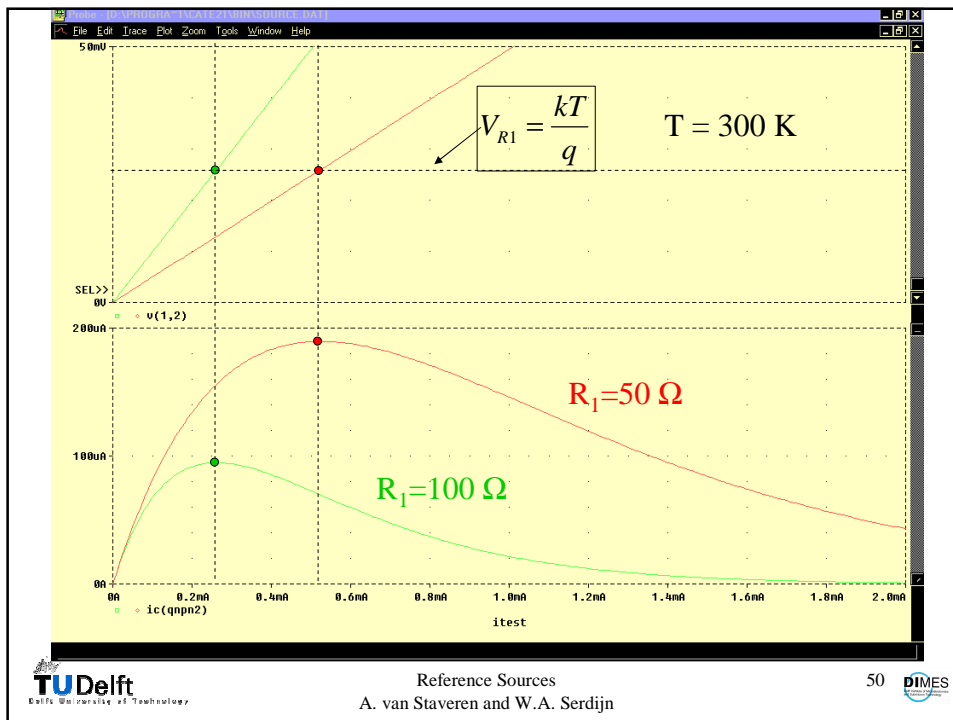
➔ Derived from current mirror

$$\ln\left(\frac{I_2}{I_{S2}}\right) = \ln\left(\frac{I_1}{I_{S1}}\right) - \frac{I_1 R_1}{kT/q}$$

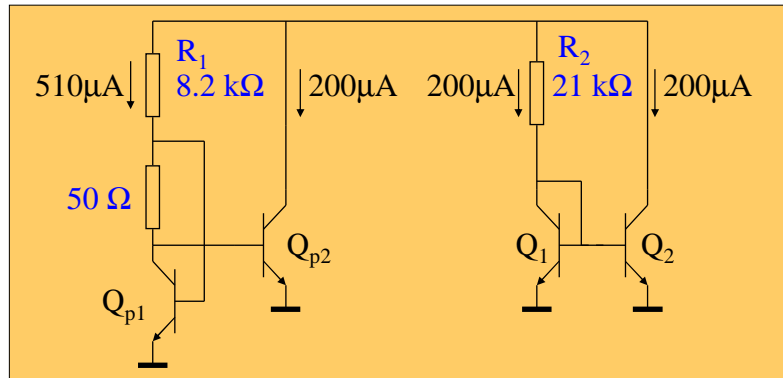
$$\frac{dI_{C2}}{dI_{C1}} = 0 \quad \text{for} \quad R \cdot I_{C1} = \frac{kT}{q}$$



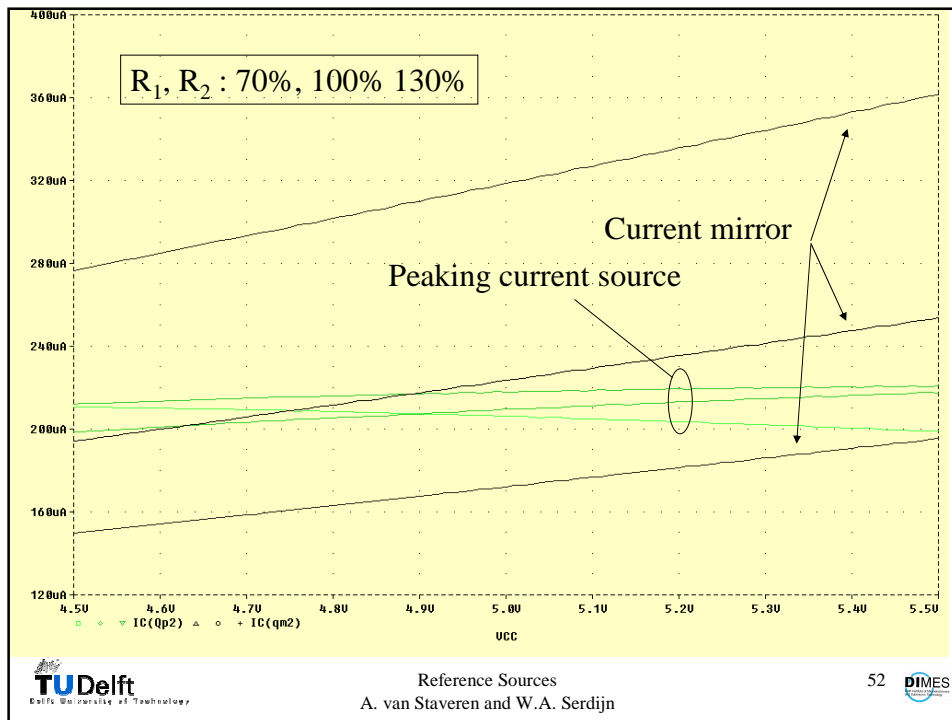
- Source I_1 can be implemented by a resistor
- R_1 relatively low ohmic and accurate ➔ a broad resistor
- R_2 relatively high ohmic and not very accurate ➔ a small resistor
- What about PSSR ?



Peaking current source vs Current mirror



- 50 must be **accurate**
- 8k2 does **not** need to be **accurate**
- 21k must be **accurate**



Conclusion/Summary

- Several configurations of voltage and current sources discussed
- **Current level** is the performance determining quality, not a 1V constraint
- Circuit design is hampered by 1V criterion ⇒ **other topologies**